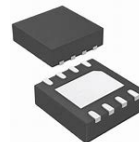


**20W,28V L band broadband Plastic RF LDMOS****ITCH17W020P3****Description**

The ITCH17W020P3 is a 20-watt, highly broadband, LDMOS transistor, in 6\*5mm DFN plastic package, supporting surface mounted on PCB through high density grounding vias. Within 1-1.7GHz, it can deliver >20W CW with high performance

- Typical broadband Class AB RF Performance (On Innegration fixture with device soldered)

V<sub>ds</sub>=28V, I<sub>dq</sub>=100mA, CW



Freq (MHz)	P1dB (dBm)	P1dB (W)	P1dB Eff (%)	P1dB Gain (dB)	P3dB (dBm)	P3dB (W)	P3dB Eff (%)
1000	43.15	20.7	61.7	15.23	43.97	25.0	65.0
1100	43.27	21.2	55.3	15.56	44.17	26.1	58.5
1200	43.69	23.4	50.8	15.51	44.57	28.6	54.0
1300	43.78	23.9	50.7	15.96	44.64	29.1	53.2
1400	43.76	23.8	52.0	16.16	44.67	29.3	54.6
1500	43.59	22.9	51.7	16.07	44.54	28.4	54.3
1600	43.37	21.7	51.3	15.95	44.28	26.8	53.3
1700	42.99	19.9	50.7	15.44	43.9	24.5	52.2

**Features**

- High Efficiency and Linear Gain Operations
- Integrated ESD Protection
- Excellent thermal stability, low HCI drift
- Large Positive and Negative Gate/Source Voltage Range for Improved Class C Operation
- Pb-free, RoHS-compliant

**Table 1. Maximum Ratings**

Rating	Symbol	Value	Unit
Drain--Source Voltage	V <sub>DSS</sub>	+65	Vdc
Gate--Source Voltage	V <sub>GS</sub>	-10 to +10	Vdc
Operating Voltage	V <sub>DD</sub>	+28	Vdc
Storage Temperature Range	T <sub>stg</sub>	-65 to +150	°C
Case Operating Temperature	T <sub>c</sub>	+150	°C
Operating Junction Temperature	T <sub>j</sub>	+225	°C

**Table 2. Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case T <sub>C</sub> = 85°C, P <sub>out</sub> =20W 1.7GHz	R <sub>θJC</sub>	0.9	°C/W

**Table 3. ESD Protection Characteristics**

Test Methodology	Class
Human Body Model (per JESD22--A114)	Class 2

**Table 4. Electrical Characteristics** (TA = 25 °C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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**DC Characteristics**

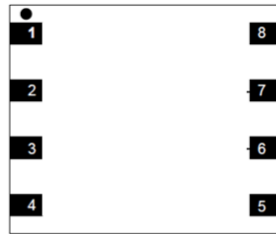


Drain-Source Voltage $V_{GS}=0$ , $I_{DS}=100\mu A$	$V_{(BR)DSS}$		65		V
Zero Gate Voltage Drain Leakage Current ( $V_{DS} = 28V$ , $V_{GS} = 0V$ )	$I_{DSS}$	—	—	1	$\mu A$
Gate--Source Leakage Current ( $V_{GS} = 11V$ , $V_{DS} = 0V$ )	$I_{GSS}$	—	—	1	$\mu A$
Gate Threshold Voltage ( $V_{DS} = 28V$ , $I_D = 600\mu A$ )	$V_{GS(th)}$	—	2	—	V
Gate Quiescent Voltage ( $V_{DD} = 28V$ , $I_D = 100mA$ , Measured in Functional Test)	$V_{GS(Q)}$	—	2.8	—	V

**Load Mismatch (In Innegration Test Fixture, 50 ohm system):**  $V_{DD} = 28Vdc$ ,  $I_{DQ} = 100mA$ ,  $f = 2100MHz$

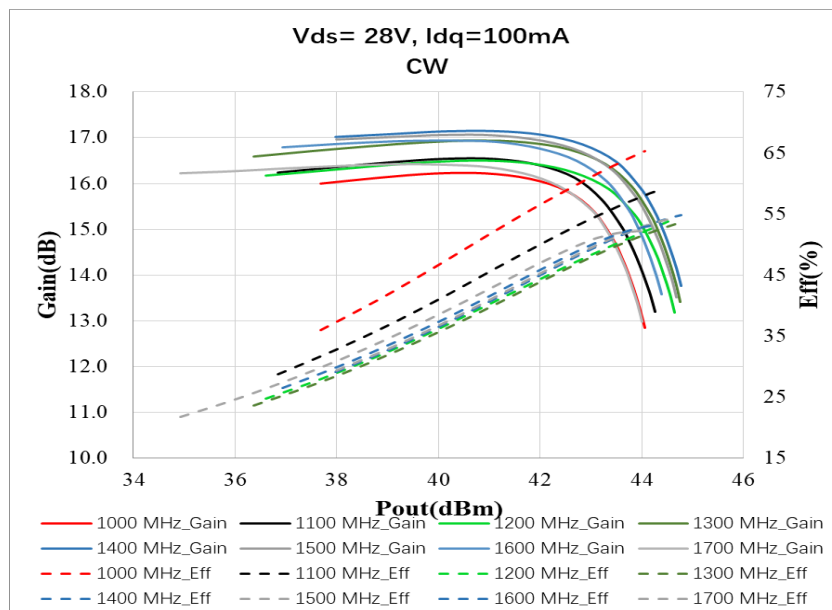
VSWR 10:1 at 10W pulse CW Output Power	No Device Degradation
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### Pin Configuration and Description(Top view)



Pin No.	Symbol	Description
1,2,3,4	RF IN/VGS	Gate Bias/RF Input
5,6, 7,8	RF OUT /VDS	RF Output, Drain Bias
Backside metal	GND	DC/RF Ground. Must be soldered to EVB ground plane over array of vias for thermal and RF performance. Solder voids under Pkg Base will result in excessive junction temperatures causing permanent damage.

### Typical performance



## Reference Circuit of Test Fixture Assembly Diagram RO4350B 20mils

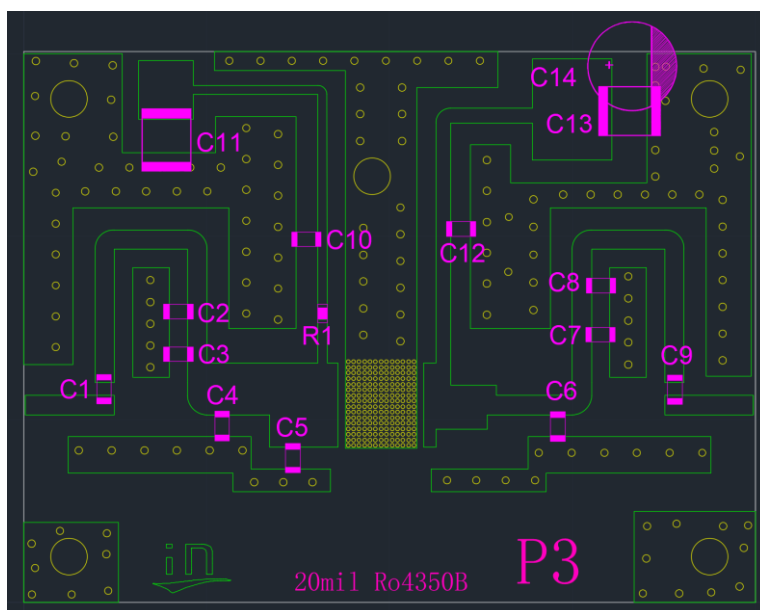


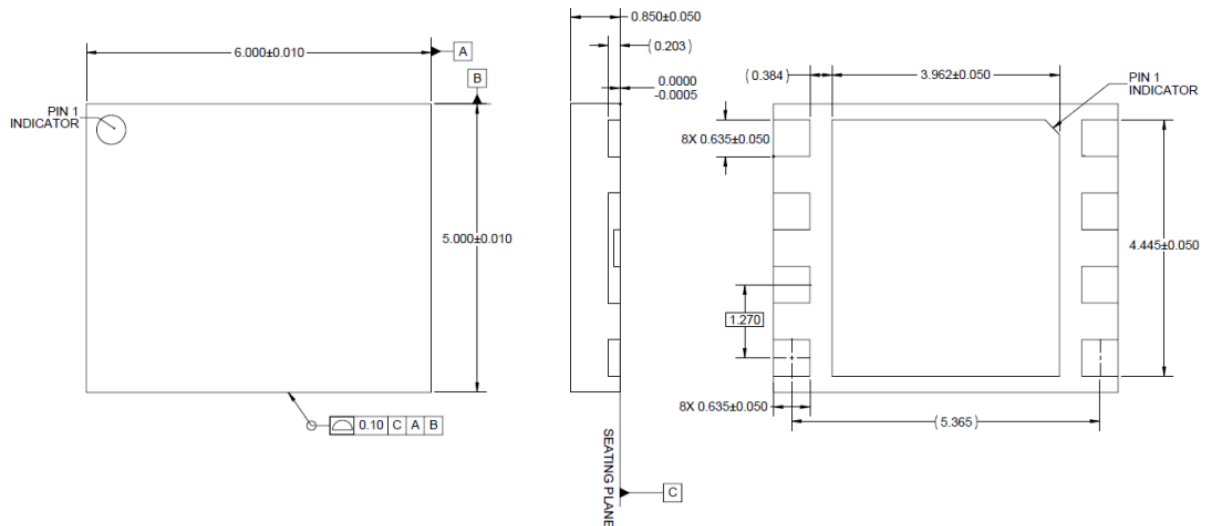
Figure 2. Test Circuit Component Layout

Reference	Footprint	Value	Quantity
C1,C9,C10,C12	0603	20 pF	4
C2,C8	0603	1 pF	2
C3	0603	2.7 pF	1
C4,C5	0603	3.9 pF	2
C6	0603	2.4 pF	1
C7	0603	1.8 pF	1
C11,C13	1210	10 uF/63V	2
C14	\	470 uF/63V	1
R1	0603	10 ohm	1
U1	P3	ITCH17W020P3	1



## Package

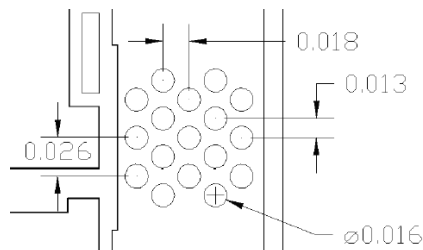
### 6\*5 DFN Package



#### Notes:

1. All dimensions are in mm. Otherwise noted, the tolerance is  $\pm 0.1$  mm.
2. Package leads are gold plated.
3. Part is mold encapsulated.

### Recommended vias layout: (all in inches)



## Revision history

Table 7. Document revision history

Date	Revision	Datasheet Status
2025/7/21	Rev 1.0	Preliminary Datasheet

### Application based on CWZ-25-12

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